

PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/441

Devices

2N3740

2N3741

Qualified Level

JAN
JANTX
JANTXV

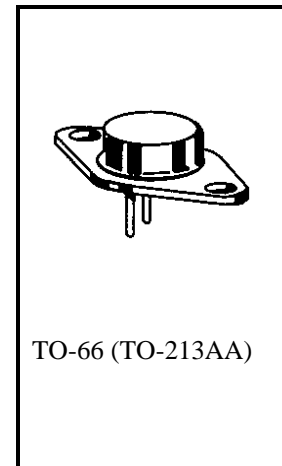
MAXIMUM RATINGS

Ratings	Symbol	2N3740	2N3741	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Base Current	I_B	2.0		Adc
Collector Current	I_C	4.0		Adc
Total Power Dissipation	P_T	@ $T_C = +25^{\circ}C$ ⁽¹⁾	25	W
		@ $T_C = +100^{\circ}C$	14	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	7.0	$^{\circ}C/W$

1) Derate linearly @ 143 mW/ $^{\circ}C$ for $T_C > +25^{\circ}C$



*See Appendix A for Package Outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc	2N3740 2N3741	$V_{(BR)CEO}$	60 80	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 40$ Vdc $V_{CE} = 60$ Vdc	2N3740 2N3741	I_{CEO}	10 10	μ Adc
Collector-Emitter Cutoff Current $V_{CE} = 60$ Vdc, $V_{BE} = 1.5$ Vdc $V_{CE} = 80$ Vdc, $V_{BE} = 1.5$ Vdc	2N3740 2N3741	I_{CEX}	300 300	η Adc
Collector-Base Cutoff Current $V_{CB} = 60$ Vdc $V_{CB} = 80$ Vdc	2N3740 2N3741	I_{CBO}	100 100	η Adc
Emitter-Base Cutoff Current $V_{EB} = 7.0$ Vdc		I_{EBO}	100	η Adc

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽²⁾				
Forward-Current Transfer Ratio I _C = 100 mA _{dc} , V _{CE} = 1.0 V _{dc} I _C = 250 mA _{dc} , V _{CE} = 1.0 V _{dc} I _C = 500 mA _{dc} , V _{CE} = 1.0 V _{dc} I _C = 1.0 A _{dc} , V _{CE} = 1.0 V _{dc} I _C = 4.0 A _{dc} , V _{CE} = 5.0 V _{dc}	h _{FE}	40 30 20 10 3.0	120	
Collector-Emitter Saturation Voltage I _C = 250 mA _{dc} , I _B = 25 mA _{dc} I _C = 1.0 A _{dc} , I _B = 125 mA _{dc}	V _{CE(sat)}		0.4 0.6	V _{dc}
Base-Emitter Voltage I _C = 250 mA _{dc} , V _{CE} = 1.0 V _{dc}	V _{BE(on)}		1.0	V _{dc}

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 100 mA _{dc} , V _{CE} = 10 V _{dc} , f = 5.0 MHz	h _{fe}	1.0	12	
Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 50 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz	h _{fe}	25	250	
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}		100	pF

SWITCHING CHARACTERISTICS

Turn-On Time V _{CC} = 30 V _{dc} ; I _C = 1.0 A _{dc} ; I _B = 0.1 A _{dc}	t _{on}		400	μs
Turn-Off Time V _{CC} = 30 V _{dc} ; I _C = 1.0 A _{dc} ; I _B = I _B = 0.1 A _{dc}	t _{off}		1.0	μs

SAFE OPERATING AREA

DC Tests T _C = +25°C, 1 Cycle, t = 1.0 s				
Test 1 V _{CE} = 6.25 V _{dc} , I _C = 4.0 A _{dc}				
Test 2 V _{CE} = 20 V _{dc} , I _C = 1.25 A _{dc}				
Test 3 V _{CE} = 50 V _{dc} , I _C = 150 mA _{dc} 2N3740 V _{CE} = 65 V _{dc} , I _C = 150 mA _{dc} 2N3741				

(2) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.



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